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DUAL P-CHANNEL 30V ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.045\Omega$; $I_D = -5.5A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



SO8

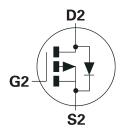
FEATURES

- · Low on-resistance
- · Fast switching speed
- Low threshold
- · Low gate drive
- Low profile SOIC package

APPLICATIONS

- Motor Drive
- · LCD backlighting

G1 S1



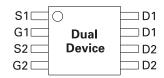
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL	
ZXMP3A16DN8TA	7''	12mm	500 units	
ZXMP3A16DN8TC	13''	12mm	2500 units	

DEVICE MARKING

ZXMP 3A16

PINOUT



Top view



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current@ $V_{GS}=10V; T_A=25^{\circ}C^{(b)(d)}$	I _D	-5.5 -4.4 -4.2	A A A
Pulsed Drain Current ^(c)	I _{DM}	-20	А
Continuous Source Current (Body Diode) ^(b)	I _S	-3.2	А
Pulsed Source Current (Body Diode) ^(c)	I _{SM}	-20	А
Power Dissipation at T _A =25°C ^{(a)(d)} Linear Derating Factor	P _D	1.25 10	W mW/°C
Power Dissipation at T _A =25°C ^{(a)(e)} Linear Derating Factor	P _D	1.8 14	W mW/°C
Power Dissipation at T _A =25°C ^{(b)(d)} Linear Derating Factor	P _D	2.1 17	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

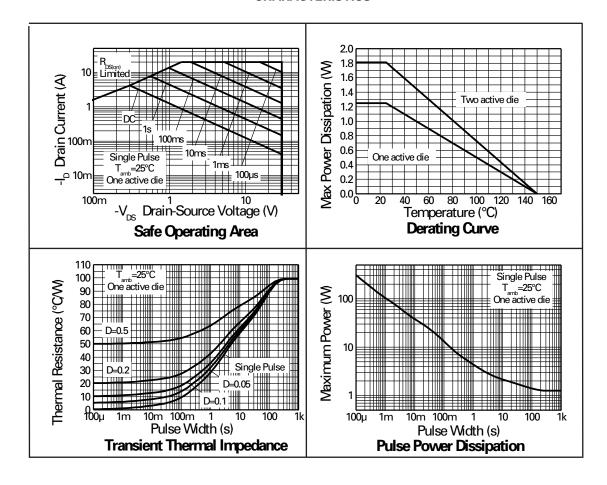
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^{(a)(d)}	$R_{\theta JA}$	100	°C/W
Junction to Ambient (b)(e)	$R_{\theta JA}$	70	°C/W
Junction to Ambient (b)(d)	$R_{\theta JA}$	60	°C/W

Notes

- (a) For a dual device surface mounted on 25mm x 25mm FR4 PCB with coverage of single sided 1oz copper in still air conditions.
- (b) For a dual device surface mounted on FR4 PCB measured at t $\leq\!10$ sec.
- (c) Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10 μ s pulse width limited by maximum junction temperature.
- (d) For a dual device with one active die.
- (e) For dual device with 2 active die running at equal power.



CHARACTERISTICS





ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25$ °C unless otherwise stated)

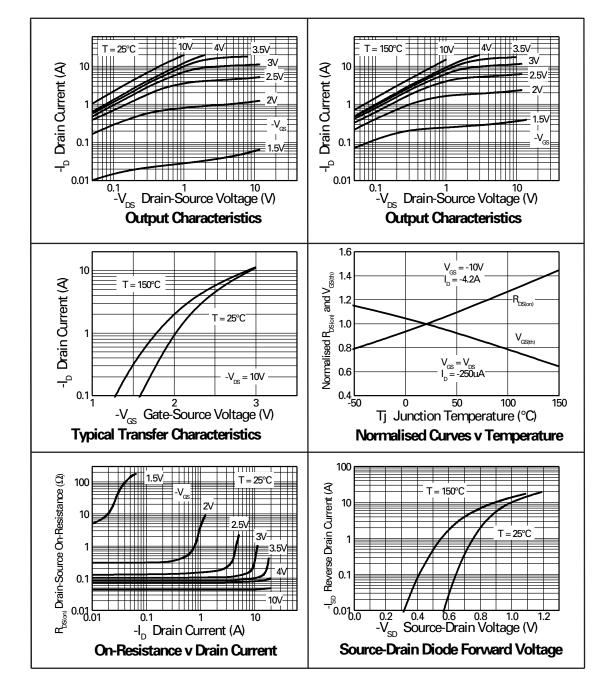
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
STATIC							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V	
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μΑ	V _{DS} =-30V, V _{GS} =0V	
Gate-Body Leakage	I _{GSS}			100	nA	$V_{GS}=\pm 20V$, $V_{DS}=0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} = V _{GS}	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.045 0.070	Ω Ω	V _{GS} =-10V, I _D =-4.2A V _{GS} =-4.5V, I _D =-3.4A	
Forward Transconductance (1)(3)	9 _{fs}		9.2		S	V _{DS} =-15V,I _D =-4.2A	
DYNAMIC (3)							
Input Capacitance	C _{iss}		1022		pF		
Output Capacitance	Coss		267		pF	V _{DS} =-15 V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance	C _{rss}		229		pF		
SWITCHING ^{(2) (3)}		•			•		
Turn-On Delay Time	t _{d(on)}		3.8		ns		
Rise Time	t _r		6.5		ns	V _{DD} =-15V, I _D =-1A	
Turn-Off Delay Time	t _{d(off)}		37.1		ns	$R_{G} = 6.0\Omega$, $V_{GS} = -10V$	
Fall Time	t _f		21.4		ns		
Gate Charge	Q_g		17.2		nC	V _{DS} =-15V,V _{GS} =-5V, I _D =-4.2A	
Total Gate Charge	Qg		29.6		nC		
Gate-Source Charge	Q _{gs}		2.8		nC	V _{DS} =-15V,V _{GS} =-10V, I _D =-4.2A	
Gate-Drain Charge	Q _{gd}		8.6		nC		
SOURCE-DRAIN DIODE	•	•		•	-	•	
Diode Forward Voltage ⁽¹⁾	V _{SD}		-0.85	-0.95	V	T _J =25°C, I _S =-3.6A, V _{GS} =0V	
Reverse Recovery Time (3)	t _{rr}		21.7		ns	T _J =25°C, I _F =-2A,	
Reverse Recovery Charge ⁽³⁾	Q _{rr}		16.1		nC	di/dt= 100A/μs	

NOTES

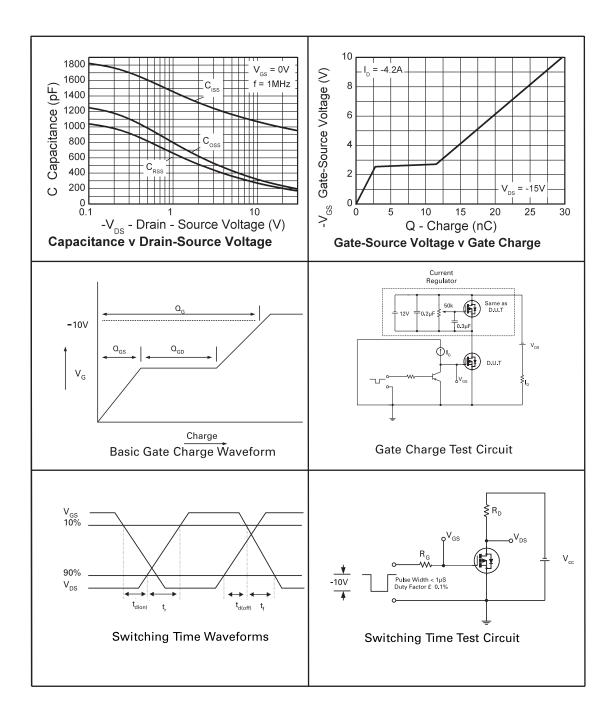
- (1) Measured under pulsed conditions. Width $\leq\!\!300\mu s.$ Duty cycle $\leq\!2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



TYPICAL CHARACTERISTICS









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or

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 - for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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Semiconductor devices are susceptible to damage by ESD. Suitable precautions should be taken when handling and transporting devices. The possible damage to devices depends on the circumstances of the handling and transporting, and the nature of the device. The extent of damage can vary from immediate functional or parametric malfunction to degradation of function or performance in use over time. Devices suspected of being affected should be replaced.

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All Zetex components are compliant with the RoHS directive, and through this it is supporting its customers in their compliance with WEEE and ELV directives.

Product status key:

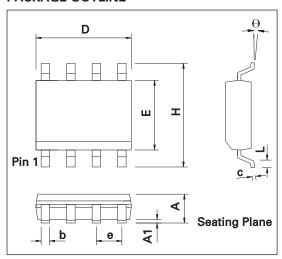
- "Preview"Future device intended for production at some point. Samples may be available
- "Active"Product status recommended for new designs
- "Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect
- "Not recommended for new designs"Device is still in production to support existing designs and production
- "Obsolete"Production has been discontinued

Datasheet status key:

- "Draft version"This term denotes a very early datasheet version and contains highly provisional
- information, which may change in any manner without notice.
- "Provisional version"This term denotes a pre-release datasheet. It provides a clear indication of anticipated performance. However, changes to the test conditions and specifications may occur, at any time and without notice.
- "Issue"This term denotes an issued datasheet containing finalized specifications. However, changes to specifications may occur, at any time and without notice.



PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES APPROX IN MILLIMETRES

PACKAGE DIMENSIONS

	Millimeters		Inches			Millimeters		Inches	
DIM	Min	Max	Min	Max	DIM	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069	е	1.27	BSC	0.050	BSC
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	С	0.19	0.25	0.008	0.010
Н	5.80	6.20	0.228	0.244	θ	0°	8°	0°	8°
Е	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-

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